TVS (for ESD protection) Peak Power Dissipation – 40 Watts @ 1 ms Surge – MMBZ15VDLT1

В	reakdow	n Voltage	•	Working Dook			Maximum Davaraa	Maximum
V _{BR} ⁽²⁾⁽⁴⁾ (Volts)			Working Peak Reverse Voltage	Maximum Reverse Leakage Current	Maximum Reverse Surge Current	Maximum Reverse Voltage @ I _{RMS} (Clamping Voltage)	Temperature Coefficient	
Min			@ l _T (mA)	V _{RWM} (Volts)	I _{RWM} I _R (nA)	I _{RSM} (Amps)	V _{RSM} (Volts)	of V _{BR} (mV/°C)
14.3	(IIIA) (VOILS)		12.8	100	1.9	21.2	12	

TVS (for ESD protection) Peak Power Dissipation – 24 Watts @ 1 ms Surge – MMBZ5V6ALT1

	Breakdov	wn Voltag	ө	Leal	everse kage rent					Max Reverse Voltage @	Maximum	
	V _{BR} ⁽²⁾⁽⁴⁾ (Volts) @ I _T			I _R @	P V _R	Z _{ZT} @ I _{ZT} Z _{ZK} @ I _{ZK}			Surge I _{RSM} Current (Clamping Voltage)		Temperature Coefficient of VBR	
Min Nom Max		(mA)	(μ A)	(v)	(ΩA) (mA)	(Ω)	(mA)	(A)	V _{RSM} (V)	(mV/°C)		
5.32	5.6	5.88	20	5.0	3.0	11	1600	0.25	3.0	8.0	1.26	

 $^{^{(2)}}$ $V_{\mbox{\footnotesize{BR}}}$ measured at pulse test current $I_{\mbox{\footnotesize{T}}}$ at an ambient temperature of 25°C.

Tuning Diodes

General Purpose, Abrupt and Hyper-Abrupt Junction, and Voltage Variable Capacitance diodes are used for tuning and control of RF circuits through UHF frequencies.

Pinout: 1-Anode, 2-NC, 3-Cathode Capacitance Ratio @ 2.0 Volts/30 Volts

The following is a listing of surface mount abrupt junction tuning diodes intended for general-purpose variable capacitance circuit applications.

	Ст	@ V _R = 4.0 V, 1.0		Cap Ratio		
Device	pF Min			V _{R(BR)R} Volts	C2/C30 Min	4.0 V, 50 MHz Typ
ABRUPT TUNING DIODES						
MMBV2101LT1	6.1	6.8	7.5	30	2.5	400
MMBV2103LT1	9.0	10	11	30	2.5	350
MMBV2104LT1	10.8	12	13.2	30	2.5	350
MMBV2105LT1	13.5	15	16.5	30	2.5	350
MMBV2107LT1	19.8	22	24.2	30	2.5	300
MMBV2108LT1	24.3	27	29.7	30	2.5	250
MMBV2109LT1	29.7	33	36.3	30	2.5	200

The following is a listing of abrupt tuning diodes that are available as dual units in a single package.

		C _T @ V _R (2)		Cap Ratio	a			
Device	pF Min	pF Max	Volts	C3/C30 Min	3.0 V, 50 MHz Min	V _{(BR)R} Volts	Device Marking	Style
ABRUPT TUNING D	IODES FOR	FM RADIO	DUAL					
MMBV432LT1	43	48.1	2.0	1.5 ⁽¹⁾	100	14	M4B	9

⁽¹⁾C2/C8

Devices listed in bold, italic are Motorola preferred devices.

 ⁽³⁾ Z_{ZT} and Z_{ZK} are measured by dividing the AC voltage drop across the device by the AC current supplied. The specified limits are I_{Z(AC)} = 0.1 I_{Z(DC)}, with AC frequency = 1 kHz.
 (4) Other voltages may be available upon request. Contact your Motorola representative.

⁽²⁾Each Diode

See Packaging Information under Technical Data Section for reel size, quantity and ordering information.

SOT-23 DIODES (continued)

Tuning Diodes (continued)

The following is a listing of hyper-abrupt tuning diodes intended for high frequency, FM radio, and TV tuner applications.

	C _T @'	C _T @ V _R (f = 1.0 MHz)			Cap Ratio @ V _R		Q					cv
Device	pF Min	pF Max	Volts	Min	Max	Volts	3.0 V Min	50 MHz Max	V _{(BR)R} Volts	Device Marking	Case Style	Curve Fig
TYPER-ABRUPT TUNING DIODES FOR TELECOMMUNICATIONS — SINGLE												
MMBV105GLT1	1.8	2.8	25	4.0	6.0	3/25	200	-	30	M4E	8	1
MMBV109LT1	26	32	3.0	5.0	6.5	3/25	200	l –	30	M4A	8	2
MMBV409LT1	26	32	3.0	1.5	2.0	3/8	200	l –	20	X5	8	3
MMBV809LT1	4.5	6.1	2.0	1.8	2.6	2/8	300	1 —	20	5K	8	4
MMBV3102LT1	20	25	3.0	4.5	_	3/25	200	<u> </u>	30	M4C	8	5
HYPER-ABRUPT T	UNING DI	ODES F	OR TEL	ECOMM	UNICAT	IONS —	DUAL					
MMBV609LT1	26	32	3.0	1.8	2.4	3/8	250	_	20	5L	9	6

See Packaging Information under Technical Data Section for reel size, quantity and ordering information.

Devices listed in bold, italic are Motorola preferred devices.